1C5415 1C5416 1C5417 1C5418 1C5419 1C5420

TECHNICAL DATA DATA SHEET 5067, REV. -

FAST RECOVERY SILICON RECTIFIER DIE

Maximum Ratings:

Characteristics	Symbol	Condition	Max.	Units
Peak Inverse Voltage	V_{RWM}	- 1C5415	50	
		1C5416	100	V (pk)
		1C5417	200	
		1C5418	400	
		1C5419	500	
		1C5420	600	
Max. Average Forward Current	I _{F(AV)}	@ 55°C	3.0	A dc
Max. Junction Temperature	TJ	-	-55 to +175	°C
Max. Storage Temperature	T _{stg}	-	-55 to +175	°C

Electrical Characteristics:

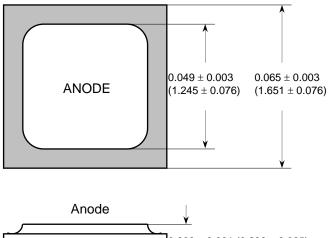
Characteristics	Symbol	Condition		Max.	_ Units _
Max. Forward Voltage Drop	V_{F1}	I _F =1.5A		1.2	V dc
	V_{F2}	I_F =9.0A dc, Pulse, T_J = 25 °C,		1.5	V (pk)
		Duty cycle \leq 2%, pulse width \leq 300 μ s			(1)
Max. Reverse Current	I _{R1}	$@V_R = V_{RWM}, Pulse, T_J = 25 °C$		1.0	μA dc
	I _{R2}	$@V_R = V_{RWM}, Pulse, T_J = 100 °C$		20	μA dc
Reverse Recovery Time	t _{rr}	10	C5415	150	ns
		10	C5416	150	
		$I_f = 500 \text{mA}, I_r = 1 \text{A}, 100$	C5417	150	
		$I_{rm} = 250 \text{mA}$	C5418	150	
		10	C5419	250	
		10	C5420	400	



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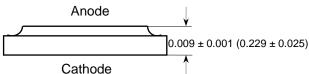
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Mechanical Dimensions: In Inches / mm



Top side metalization - Aluminum - 25 kÅ minimum. Bottom side metalization - Ti/Ni/Ag - 30 kÅ minimum

Bottom side is cathode, top side is anode.



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